

## Complementary transistor pair in a single package

### Features

- Low  $V_{CE(sat)}$
- Simplified circuit design
- Reduced component count
- Low spread of dynamic parameters

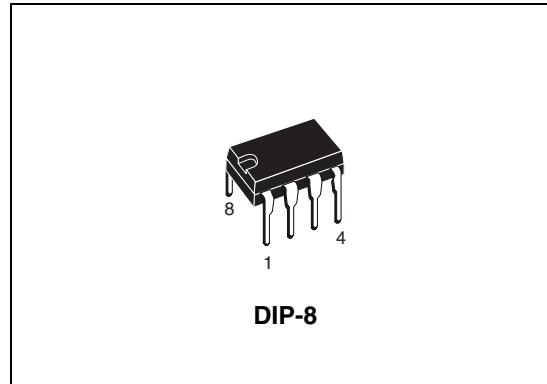
### Application

- Compact fluorescent lamp (CFL) 220 V mains

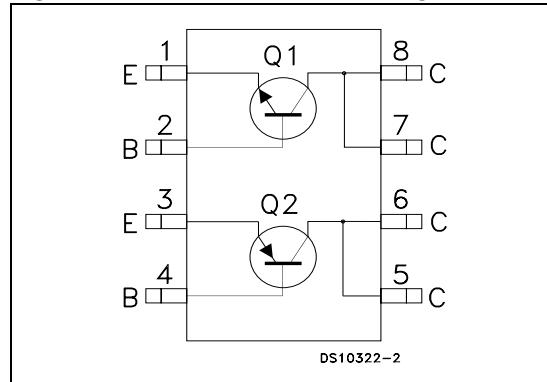
### Description

The STD815CP40 is a hybrid complementary pair of power bipolar transistors manufactured by using the high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

The STD815CP40 is housed in dual island DIP-8 package with separated terminals for higher assembly flexibility, specifically recommended to be used in a new solution for compact fluorescent lamp (CFL).



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order code	Marking	Package	Packing
STD815CP40	D815CP40	DIP-8	Tube

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		NPN	PNP	
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	700	500	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )		400	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ , $I_B = 0.75$ A, $t_p < 10$ ms)		$V_{(BR)EBO}$	V
$I_C$	Collector current		1.5	A
$I_{CM}$	Collector peak current ( $t_p < 5$ ms)		3	A
$I_B$	Base current		0.75	A
$I_{BM}$	Base peak current ( $t_p < 1$ ms)		1.5	A
$P_{TOT}$	Total dissipation at $T_{amb} = 25$ °C single transistor		2.6	W
$P_{TOT}$	Total dissipation at $T_{amb} = 25$ °C both transistors		2	W
$T_{STG}$	Storage temperature		- 65 to 150	°C
$T_J$	Max. operating junction temperature		150	°C

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJA}^{(1)}$	Thermal resistance junction-ambient (Single transistor)	48	°C/W
$R_{thJA}^{(1)}$	Thermal resistance junction-ambient (Both transistors)	63	°C/W

1. When mounted on 25mm square pad of 2 oz. copper,  $t \leq 10$  sec.

**Note:** For PNP types voltage and current values are negative.

## 2 Electrical characteristics

$T_{case} = 25^\circ\text{C}$  unless otherwise specified.

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector cut-off current ( $V_{BE} = 0$ )	For NPN: $V_{CE} = 700 \text{ V}$ $V_{CE} = 700 \text{ V} \quad T_C = 125^\circ\text{C}$ For PNP: $V_{CE} = 500 \text{ V}$ $V_{CE} = 500 \text{ V} \quad T_C = 125^\circ\text{C}$			1 5 1 5	mA mA mA mA
$V_{(BR)EBO}$	Emitter-base breakdown voltage ( $I_C = 0$ )	$I_E = 10 \text{ mA}$ For NPN: For PNP:	12 5		18 10	V V
$V_{CEO(sus)}^{(1)}$	Collector-emitter sustaining voltage ( $I_B = 0$ )	$I_C = 5 \text{ mA}$	400			V
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 0.5 \text{ A} \quad I_B = 0.1 \text{ A}$ $I_C = 0.35 \text{ A} \quad I_B = 50 \text{ mA}$			0.5 1	V V
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = 0.5 \text{ A} \quad I_B = 0.1 \text{ A}$			1	V
$h_{FE}^{(1)}$	DC current gain	$I_C = 10 \text{ mA} \quad V_{CE} = 5 \text{ V}$ $I_C = 0.35 \text{ A} \quad V_{CE} = 5 \text{ V}$ $I_C = 1 \text{ A} \quad V_{CE} = 5 \text{ V}$	10 16 4		34	
$t_r$ $t_s$ $t_f$	Resistive load Rise time Storage time Fall time	$I_C = 0.35 \text{ A} \quad V_{CC} = 125 \text{ V}$ $I_{B1} = 70 \text{ mA} \quad I_{B2} = -70 \text{ mA}$ $t_p \geq 25 \mu\text{s}$		100 2.2 0.2		ns μs μs
$t_s$ $t_f$	Inductive load Storage time Fall time	$I_C = 0.5 \text{ A} \quad I_{B1} = 0.1 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{clamp} = 300 \text{ V} \quad L = 10 \text{ mH}$		450 80		ns ns

1. Pulse test: pulse duration  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2 \%$ .

**Note:** For PNP types voltage and current values are negative

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

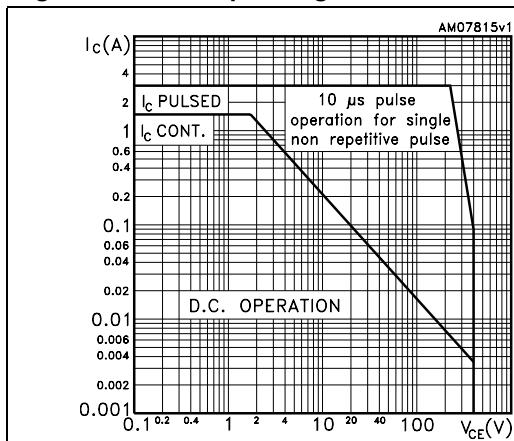


Figure 3. Derating curve

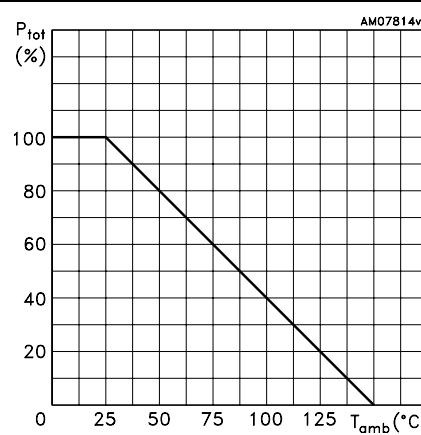


Figure 4. DC current gain NPN ( $V_{CE} = 5$  V)

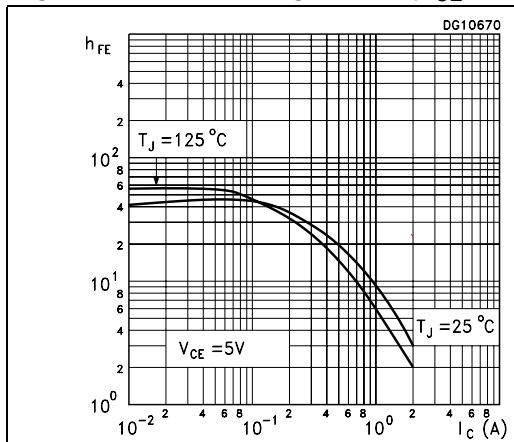


Figure 5. DC current gain PNP ( $V_{CE} = -5$  V)

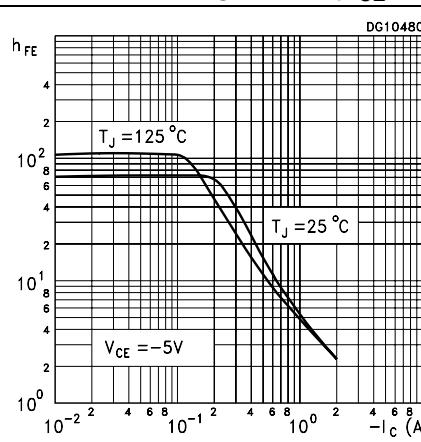


Figure 6. DC current gain NPN ( $V_{CE} = 1$  V)

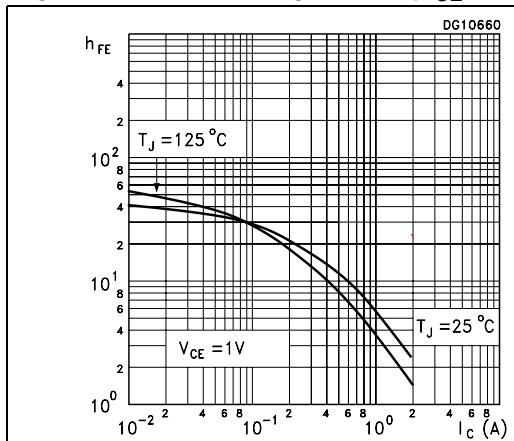
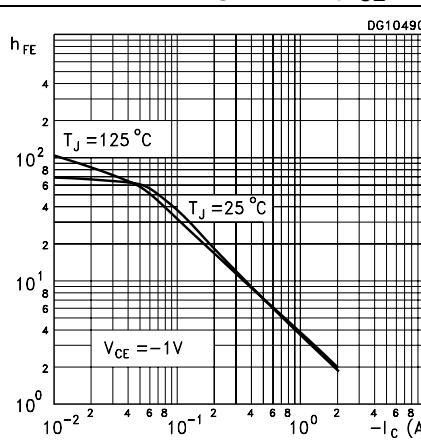
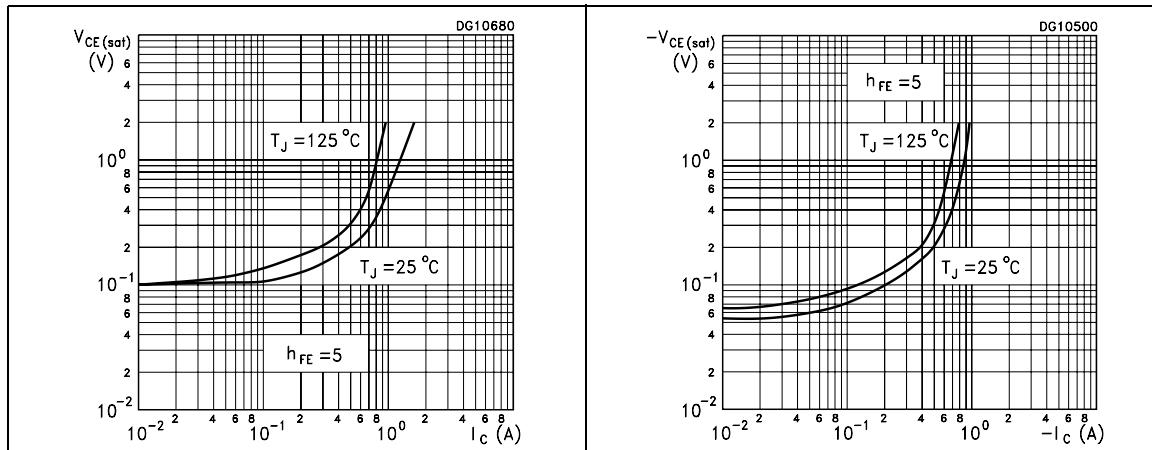


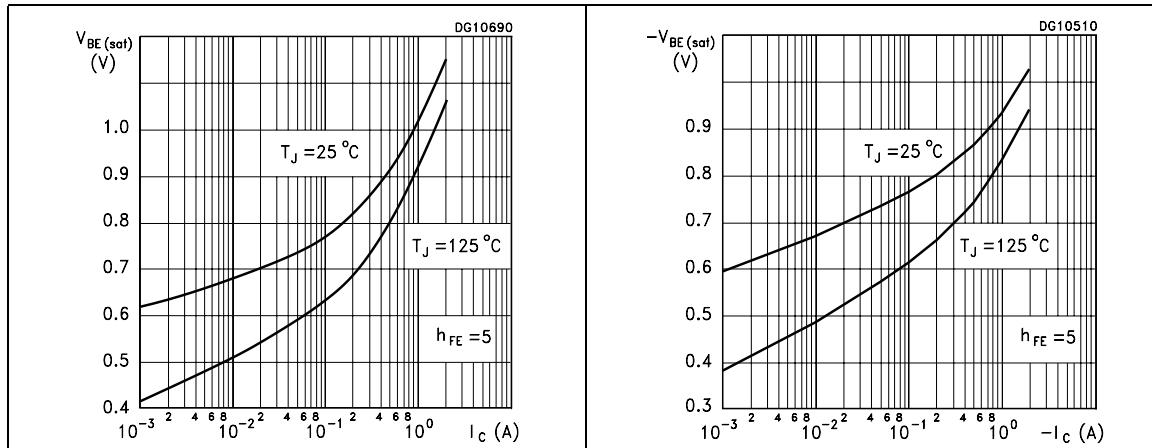
Figure 7. DC current gain PNP ( $V_{CE} = -1$  V)



**Figure 8. Collector emitter saturation voltage NPN** **Figure 9. Collector emitter saturation voltage PNP**



**Figure 10. Base emitter saturation voltage NPN**



**Figure 12. Resistive load fall time NPN**

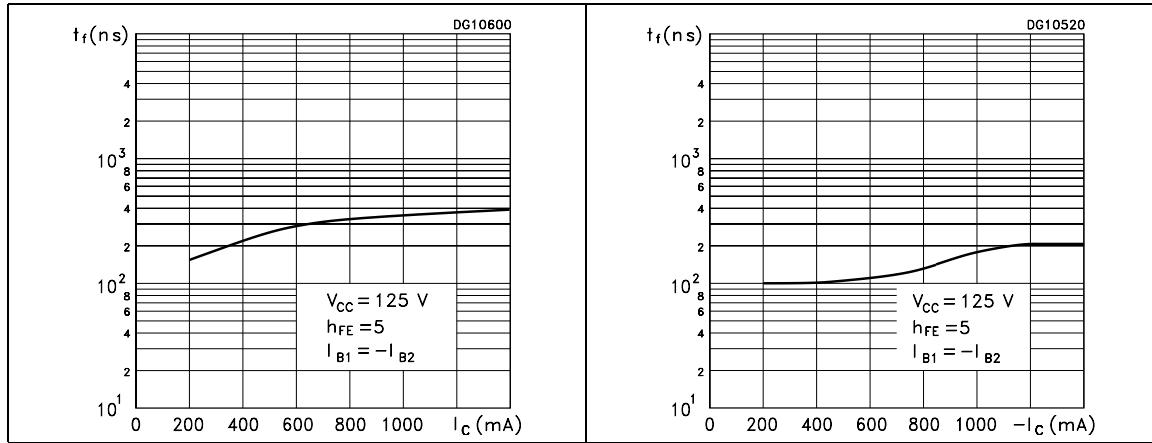


Figure 14. Resistive load storage time NPN

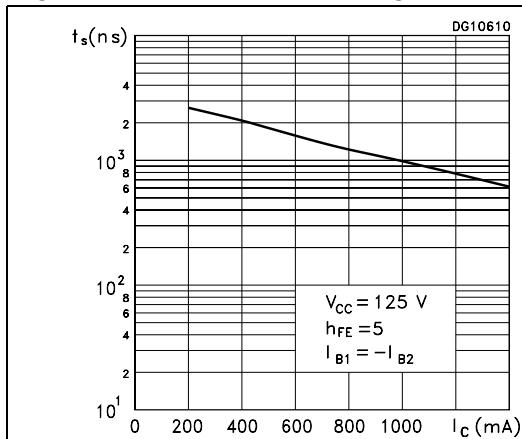


Figure 15. Resistive load storage time PNP

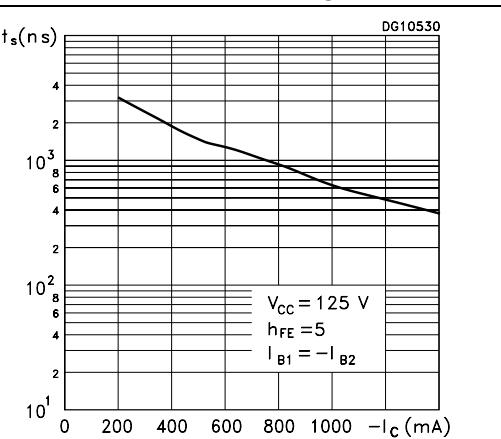


Figure 16. Inductive load fall time NPN

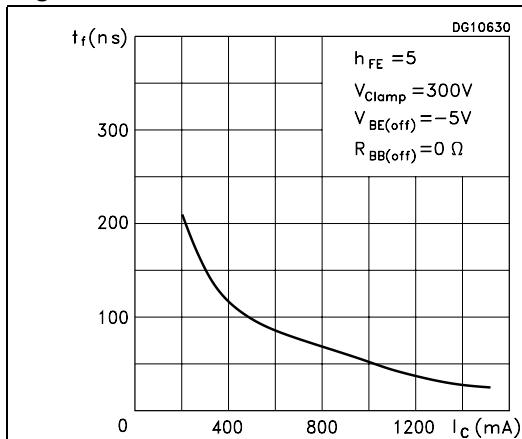


Figure 17. Inductive load fall time PNP

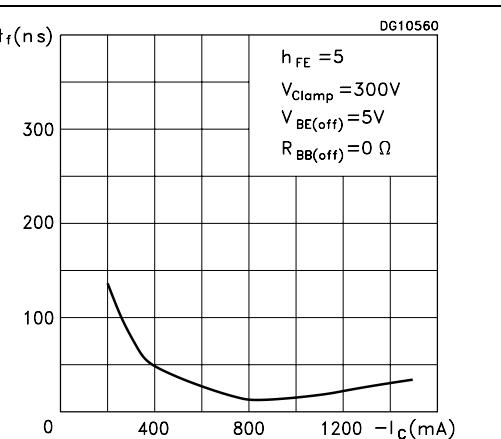


Figure 18. Inductive load storage time NPN

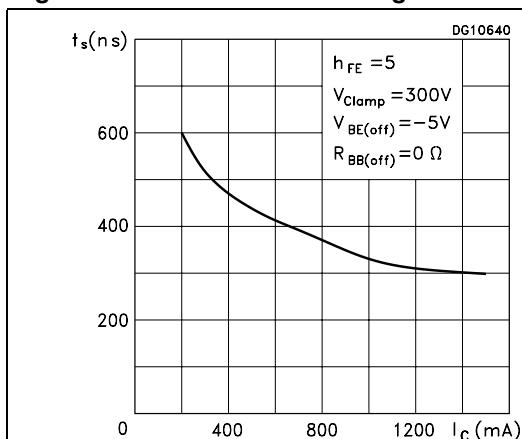


Figure 19. Inductive load storage time PNP

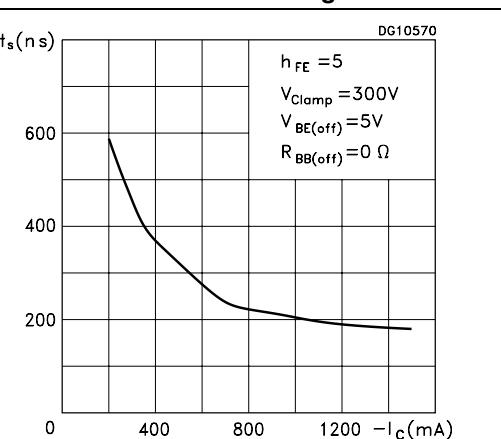


Figure 20. Reverse biased SOA (NPN)

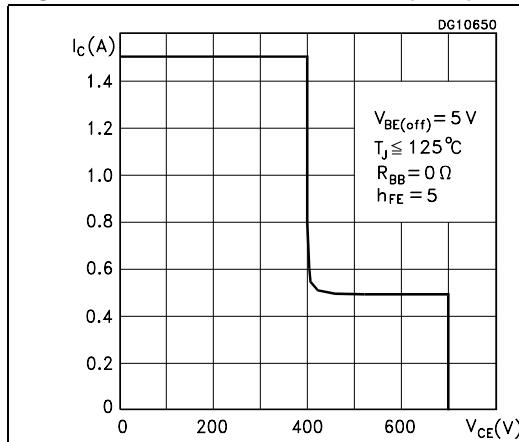
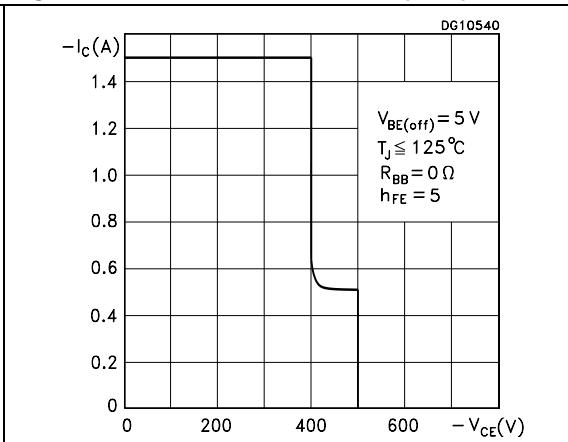


Figure 21. Reverse biased SOA (PNP)



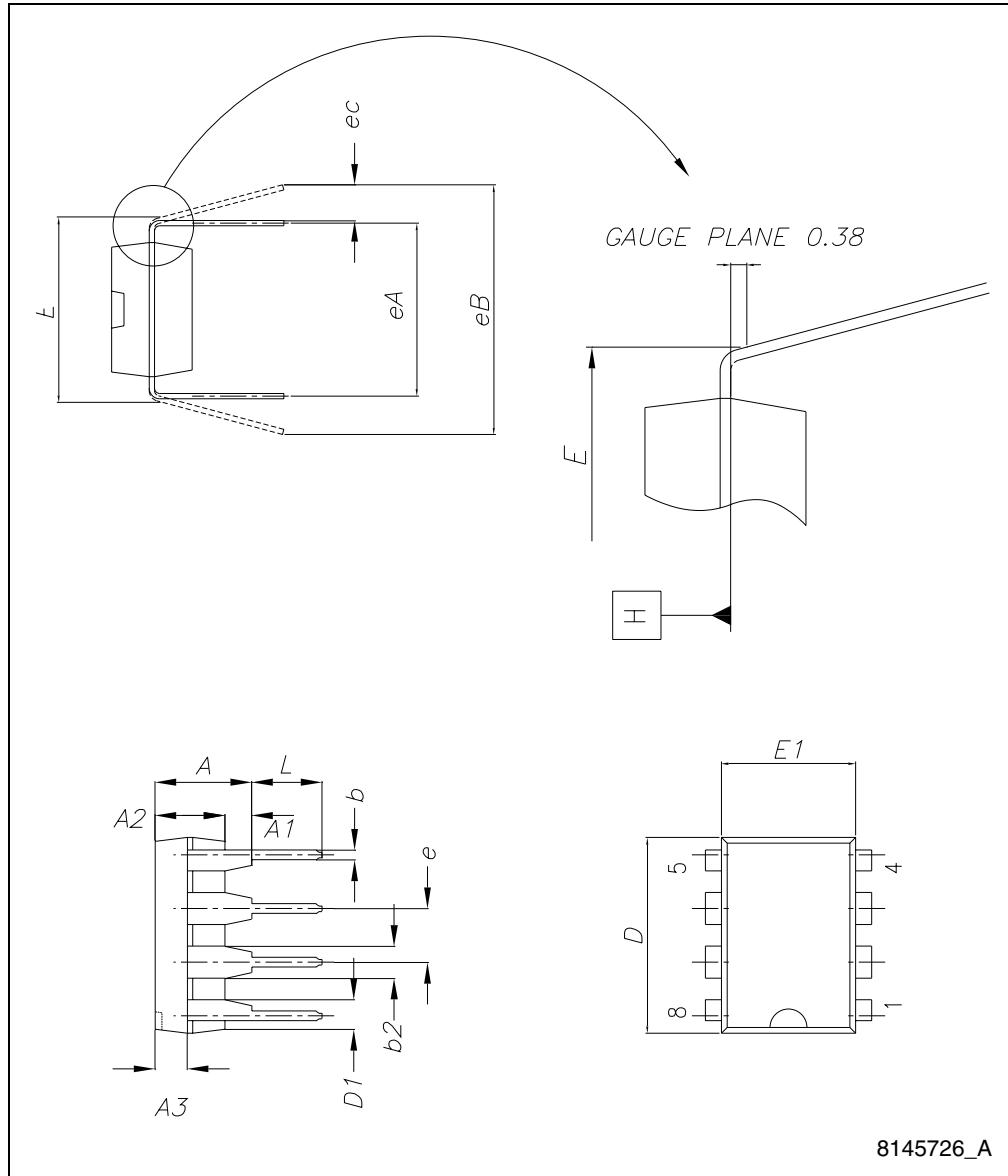
### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

**Table 5. DIP-8 mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A			4.80
A1	0.50		
A2	3.10		3.50
A3	1.40		1.60
b	0.38		0.55
b1	0.38		0.51
b2	1.47		1.57
b3	0.89		1.09
c	0.21		0.35
c1	0.20		0.30
D	9.10		9.30
D1	0.13		
E	7.62		8.25
E1	6.25		6.45
e		2.54	
eA		7.62	
eB	7.62		10.90
eC	0		1.52
L	2.92		3.81

Figure 22. Drawing dimension DIP-8



## 4 Revision history

**Table 6. Document revision history**

Date	Revision	Changes
20-Jun-2008	1	Initial release
26-May-2009	2	Updated mechanical data <i>Table 5 on page 8</i> and <i>Figure 22 on page 9</i> .
29-Jun-2010	3	Modified: <i>Table 2</i> and <i>Table 3 on page 2</i> , added <i>Section 2.1: Electrical characteristics (curves)</i> .

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